TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))	Docket No. SETI-0002DIV

In Re Application Of:

Khan et al.

Serial No.	Filing Date	Examiner	Group Art Unit
10/647,714	**8/25/2003**	**Unknown**	**Unknown**

Title: **METAL OXIDE SEMICONDUCTOR HETEROSTRUCTURE FIELD EFFECT TRANSISTOR**

Address to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

   ☐ the statement specified in 37 CFR 1.97(e);

   OR

   ☐ the fee set forth in 37 CFR 1.17(p).

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Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

☐ A check in the amount of is attached.

☒ The Director is hereby authorized to charge and credit Deposit Account No. **500999** as described below.

- ☐ Charge the amount of
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Dated: **October 30, 2003**

John W. LaBatt
Reg. No. 48,301
Cust mer No. 23550

cc:

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.	SERIAL NO.
SETI-0002	09/966,559
Khan et al.	
FILING	GROUP
09/27/2001	2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

			"Optoelectronic GaN-based Field Effect Transistors," M. S. Shur et al., SPIE, Vol. 2397, pp. 294-303, Feb. 7, 1995.
			"High Pinch-off Voltage AlGaN-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, pp. 377-380, Charlottesville, VA, Dec. 1997.

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

			"DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binari et al., Inst. Phys. Conf. Ser. No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.
			"GaN - AlxGa1-xN Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposium Proceedings Vol . 281 (1993), pp.769-774.

EXAMINER	DATE CONSIDERED

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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

			"Low Dark Current Transparent Schottky Barrier UV Detectors," G. Simin et al., ICNS3, Montpellier, June 1999.

EXAMINER	DATE CONSIDERED

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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
SETI-006	09/966559
Applicant(s)	
Khan et al.	
Filing Date	**Group Art Unit**
9/27/2001	2818

*EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
		Ren, F. et al., "Effect f temperature on Ga2O3(Gd2O3)/GaN metal-oxide-semiconductor field-effect transistors," Applied Physics Letters, Vol. 73, No. 26, 28 December 1998, pp. 3893-3895.
		Gaska, R. et al., "Electron mobility in modulation-doped AlGaN-GaN heterostructures," Applied Physics Letters, Vol. 74, No. 2, 11 January 1999, pp. 287-289.
		Khan, M.A. et al., "Current/voltage characteristic collapse in AlGaN/GaN heterostructure insulated gate field effect transistors at high drain bias," Electronics Letters, Vol. 30, No. 25, 8 December 1994, pp. 2175-2176.
		Carrano, J.C. et al., "Very low dark current metal-semiconductor-metal ultraviolet photodetectors fabricated on single-crystal GaN epitaxial layers," Applied Physics Letters, Vol. 70, No. 15, 14 April 1997, pp. 1992-1994.
		Chen, Q. et al., "Schottky barrier detectors on GaN for visible-blind ultraviolet detection," Applied Physics Letters, Vol. 70, No. 17, 28 April 1997, pp. 2277-2279.
		Khan, M.A. et al., "AlGaN/GaN metal-oxide-semiconductor heterostructure field-effect transistors on SiC substrates," Applied Physics Letters, Vol. 77, No. 9, 28 August 2000, pp. 1339-1341.
		Shur, M.S. and Khan, M.A., "GaN and AlGaN Devices: Field Effect Transistors and Photodetectors," Gordon and Breach Science Publishers, Series Optoelectronic Properties of Semiconductors and Superlattices, Vol. 7 GaN and Related Materials II, pp. 47-92, S. Pearton, Editor (1999).
		Shur, M.S. and Khan, M.A., "Wide Band Gap Semiconductors. Good Results and Great Expectations," Paper presented at 23rd Int. Symp. Compound Semiconductors, St. Petersburg, Russia, 23-27 September 1996, pp. 25-31.
		Khan, M.A. et al., "AlGaN/GaN Metal Oxide Semiconductor Heterostructure Field Effect Transistor," IEEE Electron Device Letters, Vol. 21, No. 2, February 2000, pp. 63-65.

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